Optimal nano-dimensional channel of gaas finFET transistor

Ahmed Mahmood, Waheb A. Jabbar, Wasan Kadhim Saad, Yasir Hashim, Hadi Bin Manap

1. Faculty of Engineering Technology, Universiti Malaysia Pahang, Gambang, Kuantan, Pahang, 26300, Malaysia
2. Al-Furat Al-Awsat Technical University, Engineering Technical College, Najaf, Iraq
3. Computer Engineering Department, Faculty of Engineering, Ishik University, Erbil-Kurdistan, Iraq

Abstract:
This paper investigates the optimal nano-dimensions channel for Gallium Arsenide Fin Field Effect Transistor (GaAs-FinFET) based on I ON /I OFF ratio and subthreshold swing (SS). The impact of reducing channel dimensions (length, width, and oxide thickness) on GaAs-FinFET performance has been evaluated in terms of various electrical characteristics (I ON /I OFF , SS, VT and DIBL). The MuGFET simulation tool is used in this study to simulate the current-voltage characteristics for different dimensions of channel. According to highest I ON /I OFF ratio, and nearest SS to the ideal SS, the best channel dimensions of GaAs-FinFET are designed. The results show that the best performance can be achieved with the lowest scaling factor, K of 0.25, when the length is 40 nm, the width is 3 nm, and the oxide thickness is 1 nm.

Keywords: FinFETs; Gallium arsenide; Tools; Nanoscale devices

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